General Purpose TransistorsNPN Silicon

COLLECTOR

3

BASE

2

EMITTER

mAdc

MAXIMUM RATINGS

BC847 BC848 BC850 **BC849** Rating Symbol **BC846** Unit Collector-Emitter Voltage VCEO ٧ Collector-Base Voltage **V**СВО 80 50 30 ٧ ٧ Emitter-Base Voltage 6.0 6.0 5.0 **VEBO**

IC

100

100

100

Collector Current — Continuous THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (1) T _A = 25°C Derate above 25°C	PD	225 1.8	mW mW/°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (2) T _A = 25°C Derate above 25°C	PD	300 2.4	mW mW/°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

DEVICE MARKING

BC846ALT1 = 1A; BC846BLT1 = 1B; BC847ALT1 = 1E; BC847BLT1 = 1F; BC847CLT1 = 1G; BC848ALT1 = 1J; BC848BLT1 = 1K; BC848CLT1 = 1L

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic			Min	Тур	Max	Unit	
OFF CHARACTERISTICS							
Collector-Emitter Breakdown Voltage (I _C = 10 mA)	BC846A,B BC847A,B,C, BC850A,B,C BC848A,B,C, BC849A,B,C	V _(BR) CEO	65 45 30	N AI-02	ec <u>-</u> co	V	
Collector-Emitter Breakdown Voltage (I _C = 10 μA, V _{EB} = 0)	BC846A,B BC847A,B,C, BC850A,B,C BC848A,B,C, BC849A,B,C	V _(BR) CES	80 50 30	_ _ _		V	
Collector-Base Breakdown Voltage (I _C = 10 μA)	BC846A,B BC847A,B,C, BC850A,B,C BC848A,B,C, BC849A,B,C	V(BR)CBO	80 50 30	_ _ _		V	
Emitter-Base Breakdown Voltage (I _E = 1.0 μA)	BC846A,B BC847A,B,C BC848A,B,C, BC849A,B,C, BC850A,B,C	V(BR)EBO	6.0 6.0 5.0	_ _ _		V	
Collector Cutoff Current (V _{CB} = 30 V) (V _{CB} = 30 V,	Γ _A = 150°C)	ICBO	_ _	_	15 5.0	nA μA	

1.0 x 0.75 x 0.062 in 2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

hermal Clad is a trademark of the Bergquist Company.

Preferred devices are Motorola recommended choices for future use and best overall value.



BC846, BC847 and BC848 are Motorola Preferred Devices



CASE 318-08, STYLE 6 SOT-23 (TO-236AB)

BC846ALT1, BLT1 BC847ALT1, BLT1, CLT1 thru BC850ALT1, BLT1, CLT1

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted) (Continued)

	Characteristic	Symbol	Min	Тур	Max	Unit
ON CHARACTERISTICS						
DC Current Gain (I _C = 10 μA, V _{CE} = 5.0 V)	BC846A, BC847A, BC848A BC846B, BC847B, BC848B BC847C, BC848C	hFE		90 150 270		_
$(I_C = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V})$	BC846A, BC847A, BC848A, BC849A, BC850A BC846B, BC847B, BC848B, BC849B, BC850B BC847C, BC848C, BC849C, BC850C		110 200 420	180 290 520	220 450 800	
Collector-Emitter Saturation Voltage (I _C = 10 mA, I _B = 0.5 mA) (I _C = 100 mA, I _B = 5.0 mA)		V _{CE(sat)}		_	0.25 0.6	V
Base-Emitter Saturation Voltage ($I_C = 10$ mA, $I_B = 0.5$ mA) ($I_C = 100$ mA, $I_B = 5.0$ mA)		V _{BE(sat)}	_	0.7 0.9	_	V
Base-Emitter Voltage (I _C = 2.0 mA, V_{CE} = 5.0 V) (I _C = 10 mA, V_{CE} = 5.0 V)		VBE(on)	580 —	660 —	700 770	mV
SMALL-SIGNAL CHARACTERISTICS						

Current-Gain — Bandwidth Product (I _C = 10 mA, V _{CE} = 5.0 Vdc, f = 100 MHz)		fΤ	100	1		MHz
Output Capacitance (V _{CB} = 10 V,	f = 1.0 MHz)	C _{obo}			4.5	pF
Noise Figure (I _C = 0.2 mA, V _{CE} = 5.0 Vdc, R _S = 2.0 k Ω , f = 1.0 kHz, BW = 200 Hz)	BC846A, BC847A, BC848A BC846B, BC847B, BC848B BC847C, BC848C BC849A,B,C, BC850A,B,C	NF			10 4.0	dB

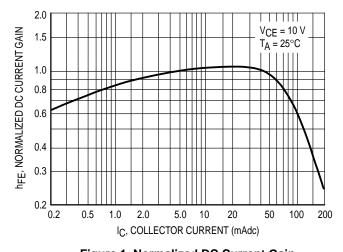


Figure 1. Normalized DC Current Gain

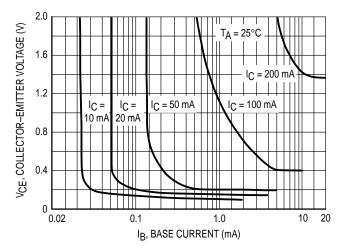


Figure 3. Collector Saturation Region

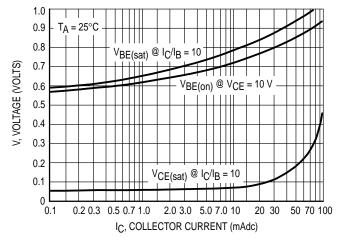


Figure 2. "Saturation" and "On" Voltages

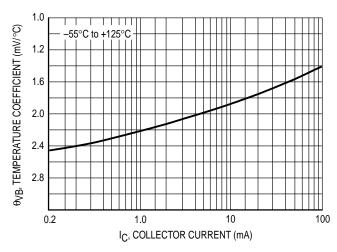


Figure 4. Base–Emitter Temperature Coefficient

BC846ALT1, BLT1 BC847ALT1, BLT1, CLT1 thru BC850ALT1, BLT1, CLT1 BC847/BC848

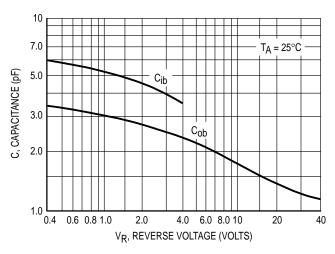


Figure 5. Capacitances

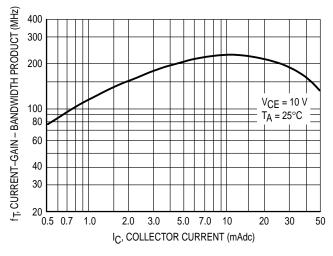


Figure 6. Current-Gain - Bandwidth Product

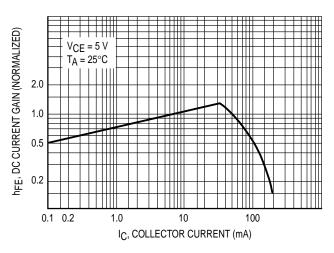


Figure 7. DC Current Gain

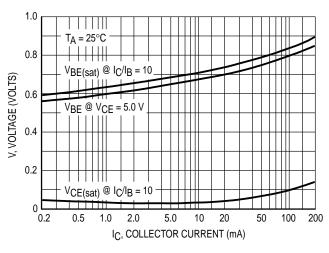


Figure 8. "On" Voltage

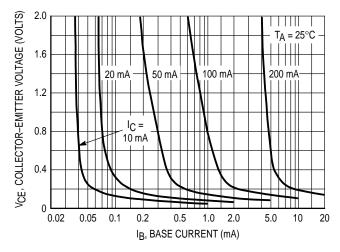


Figure 9. Collector Saturation Region

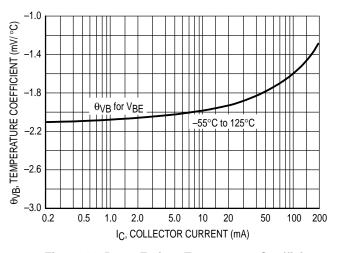


Figure 10. Base-Emitter Temperature Coefficient

BC846ALT1, BLT1 BC847ALT1, BLT1, CLT1 thru BC850ALT1, BLT1, CLT1 BC846

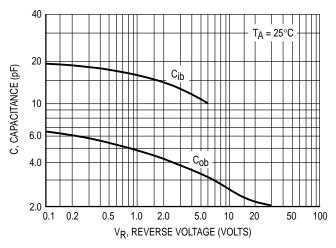


Figure 11. Capacitance

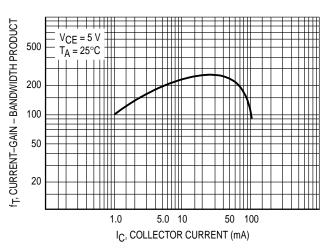
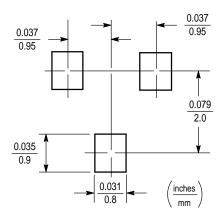


Figure 12. Current-Gain - Bandwidth Product

BC846ALT1, BLT1 BC847ALT1, BLT1, CLT1 thru BC850ALT1, BLT1, CLT1 INFORMATION FOR USING THE SOT-23 SURFACE MOUNT PACKAGE

MINIMUM RECOMMENDED FOOTPRINT FOR SURFACE MOUNTED APPLICATIONS

Surface mount board layout is a critical portion of the total design. The footprint for the semiconductor packages must be the correct size to insure proper solder connection interface between the board and the package. With the correct pad geometry, the packages will self align when subjected to a solder reflow process.



SOT-23

SOT-23 POWER DISSIPATION

The power dissipation of the SOT–23 is a function of the pad size. This can vary from the minimum pad size for soldering to a pad size given for maximum power dissipation. Power dissipation for a surface mount device is determined by $T_{J(max)}$, the maximum rated junction temperature of the die, $R_{\theta JA}$, the thermal resistance from the device junction to ambient, and the operating temperature, T_A . Using the values provided on the data sheet for the SOT–23 package, P_D can be calculated as follows:

$$P_D = \frac{T_{J(max)} - T_A}{R_{\theta JA}}$$

The values for the equation are found in the maximum ratings table on the data sheet. Substituting these values into the equation for an ambient temperature T_A of $25^{\circ}C$, one can calculate the power dissipation of the device which in this case is 225 milliwatts.

$$P_D = \frac{150^{\circ}C - 25^{\circ}C}{556^{\circ}C/W} = 225 \text{ milliwatts}$$

The 556°C/W for the SOT–23 package assumes the use of the recommended footprint on a glass epoxy printed circuit board to achieve a power dissipation of 225 milliwatts. There are other alternatives to achieving higher power dissipation from the SOT–23 package. Another alternative would be to use a ceramic substrate or an aluminum core board such as Thermal Clad™. Using a board material such as Thermal Clad, an aluminum core board, the power dissipation can be doubled using the same footprint.

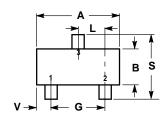
SOLDERING PRECAUTIONS

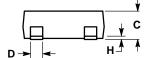
The melting temperature of solder is higher than the rated temperature of the device. When the entire device is heated to a high temperature, failure to complete soldering within a short time could result in device failure. Therefore, the following items should always be observed in order to minimize the thermal stress to which the devices are subjected.

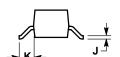
- Always preheat the device.
- The delta temperature between the preheat and soldering should be 100°C or less.*
- When preheating and soldering, the temperature of the leads and the case must not exceed the maximum temperature ratings as shown on the data sheet. When using infrared heating with the reflow soldering method, the difference shall be a maximum of 10°C.
- The soldering temperature and time shall not exceed 260°C for more than 10 seconds.
- When shifting from preheating to soldering, the maximum temperature gradient shall be 5°C or less.
- After soldering has been completed, the device should be allowed to cool naturally for at least three minutes.
 Gradual cooling should be used as the use of forced cooling will increase the temperature gradient and result in latent failure due to mechanical stress.
- Mechanical stress or shock should not be applied during cooling.
- * Soldering a device without preheating can cause excessive thermal shock and stress which can result in damage to the device.

BC846ALT1, BLT1 BC847ALT1, BLT1, CLT1 thru BC850ALT1, BLT1, CLT1

PACKAGE DIMENSIONS







CASE 318-08 ISSUE AE SOT-23 (TO-236AB)

- DIMENSIONING AND TOLERANCING PER ANSI
- CONTROLLING DIMENSION: INCH
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.1102	0.1197	2.80	3.04	
В	0.0472	0.0551	1.20	1.40	
С	0.0350	0.0440	0.89	1.11	
D	0.0150	0.0200	0.37	0.50	
G	0.0701	0.0807	1.78	2.04	
Н	0.0005	0.0040	0.013	0.100	
J	0.0034	0.0070	0.085	0.177	
K	0.0180	0.0236	0.45	0.60	
L	0.0350	0.0401	0.89	1.02	
S	0.0830	0.0984	2.10	2.50	
٧	0.0177	0.0236	0.45	0.60	

STYLE 6:

PIN 1. BASE

- EMITTER
- 3. COLLECTOR

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How to reach us:

USA/EUROPE: Motorola Literature Distribution;

P.O. Box 20912; Phoenix, Arizona 85036. 1-800-441-2447

MFAX: RMFAX0@email.sps.mot.com - TOUCHTONE (602) 244-6609 INTERNET: http://Design-NET.com

JAPAN: Nippon Motorola Ltd.; Tatsumi-SPD-JLDC, Toshikatsu Otsuki, 6F Seibu-Butsuryu-Center, 3-14-2 Tatsumi Koto-Ku, Tokyo 135, Japan. 03-3521-8315

HONG KONG: Motorola Semiconductors H.K. Ltd.; 8B Tai Ping Industrial Park, 51 Ting Kok Road, Tai Po, N.T., Hong Kong. 852-26629298

